

LED CHIP CP940-40

SPECIFICATION OF LED CHIP  
CP940-40  
[INFRARED]

1) Commodity Type and Physical Characteristics.

- |                      |             |                  |            |
|----------------------|-------------|------------------|------------|
| 1. Material          | GaAlAs/GaAs |                  |            |
| 2. Electrode         | Top Side    | P (anode) side   | : Au Alloy |
|                      | Bottom Side | N (cathode) side | : Au Alloy |
| 3. Electrode Pattern | Fig.1       |                  |            |
| 4. Chip Size         | Fig.2       |                  |            |
| 5. Chip Thickness    | Fig.2       |                  |            |
| 6. Emission Area     | Fig.2       |                  |            |

2) Electro-Optical Characteristics

Parameters	Symbol	Condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=20mA		1.22	1.35	V
		If=50mA		1.25	1.45	
Reverse Current	Ir	Vr=5V			10	uA
Power Intensity	Po	If=20mA	1.5	2.5		mW
		If=50mA	3.8	6.2		
Peak Wavelength	$\lambda_P$	If=20mA	930	940	955	nm
Spectral Radiation Bandwidth	$\Delta\lambda$	If=20mA		50		nm
RiseTime	tr	If=20mA		1000		ns
FallTime	tf	If=20mA		500		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.(Ta=25°C)

[Unit : um]

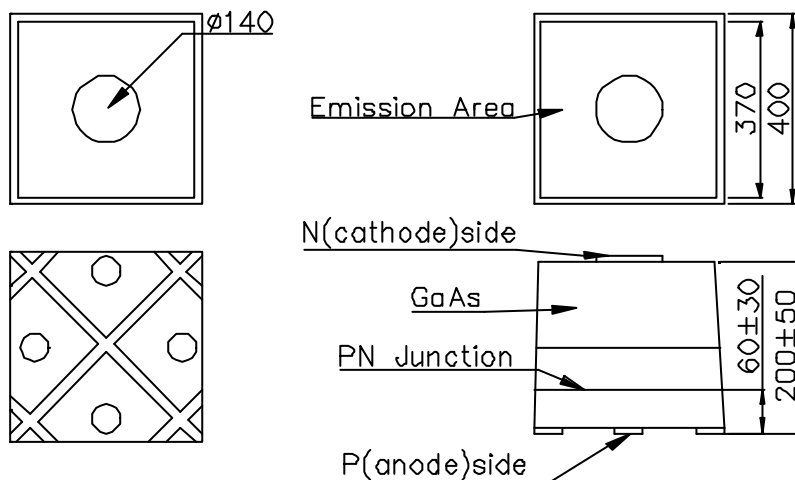


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area

